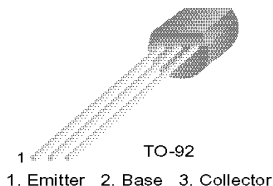
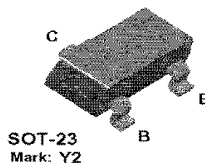


SS8550



MMBT8550S



2W Output Amplifier of Portable Radios in Class B Push-pull Operation.

- Complimentary to 8050
- Collector Current: $I_C = 1.5A$
- Collector Power Dissipation: $P_C = 2W$ ($T_C = 25^\circ C$)

Absolute Maximum Ratings $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CBO}	Collector-Base Voltage	- 40	V
V_{CEO}	Collector-Emitter Voltage	- 25	V
V_{EB0}	Emitter-Base Voltage	- 8	V
I_C	Collector Current	- 1.5	A
P_C	Collector Power Dissipation	1	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	-65 ~ 150	$^\circ C$

Electrical Characteristics $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = -100\mu A, I_E = 0$	- 40			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -2mA, I_B = 0$	- 25			V
BV_{EB0}	Emitter-Base Breakdown Voltage	$I_E = -100\mu A, I_C = 0$	- 8			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = -35V, I_E = 0$			-100	nA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = -6V, I_C = 0$			-100	nA
h_{FE1} h_{FE2} h_{FE3}	DC Current Gain	$V_{CE} = -1V, I_C = -5mA$ $V_{CE} = -1V, I_C = -100mA$ $V_{CE} = -1V, I_C = -800mA$	45 35 40	170 160 60	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -800mA, I_B = -80mA$		-0.28	-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -800mA, I_B = -80mA$		-0.98	-1.2	V
$V_{BE(on)}$	Base-Emitter on Voltage	$V_{CE} = -1V, I_C = -10mA$		-0.66	-1.0	V
C_{ob}	Output Capacitance	$V_{CB} = -10V, I_E = 0$ $f = 1MHz$		15		pF
f_T	Current Gain Bandwidth Product	$V_{CE} = -10V, I_C = -50mA$	100	200		MHz

h_{FE} Classification OF DIP

Classification	B	C	D
h_{FE2}	85 ~ 160	120 ~ 200	160 ~ 320

h_{FE} Classification OF SMD

Classification	L	H	J
h_{FE}	120 ~ 200	200 ~ 350	300 ~ 400

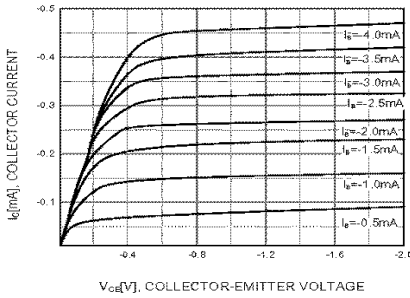


Figure 1. Static Characteristic

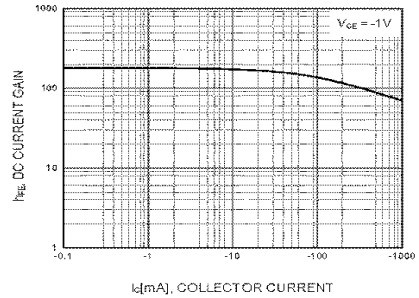


Figure 2. DC current Gain

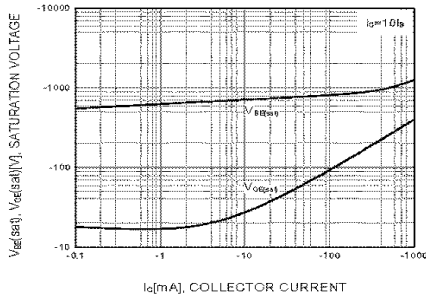


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

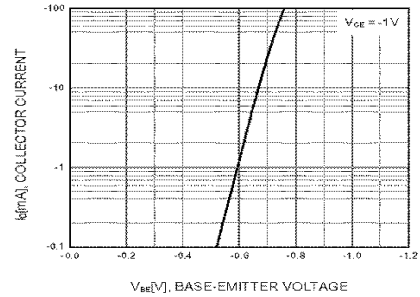


Figure 4. Base-Emitter On Voltage

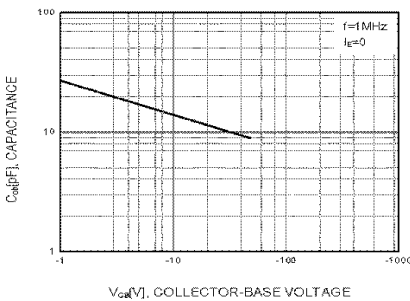


Figure 5. Collector Output Capacitance

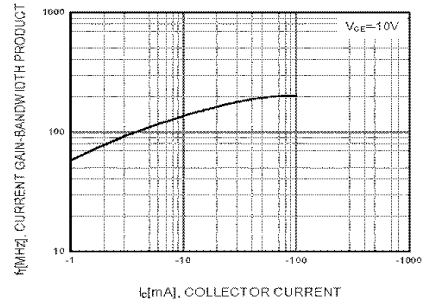
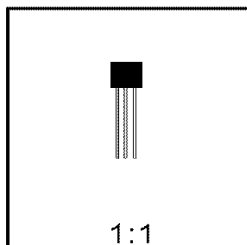
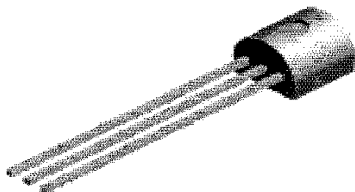


Figure 6. Current Gain Bandwidth Product

TO-92



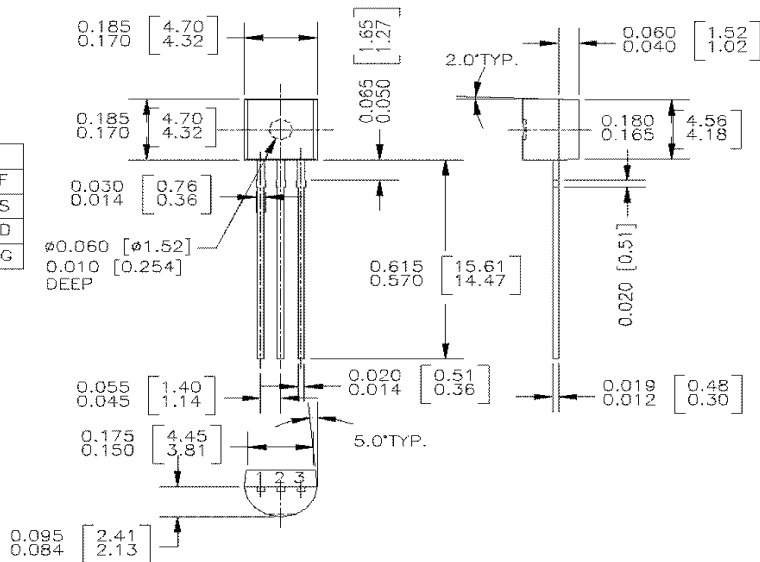
Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

TO-92 (92,94,96)

PIN	92		94		96	
	B	F	B	F	B	F
1	E	D	E	D	B	S
2	B	S	C	G	E	D
3	C	G	B	S	C	G





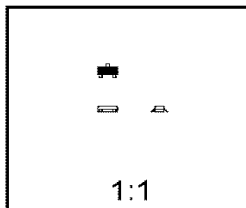
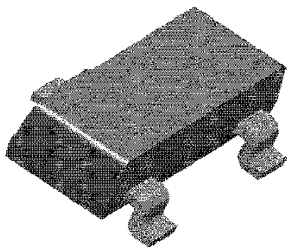
福摩斯
FU MO SI

SS8050 MM8050S

PNP Epitaxial silicon Transistor



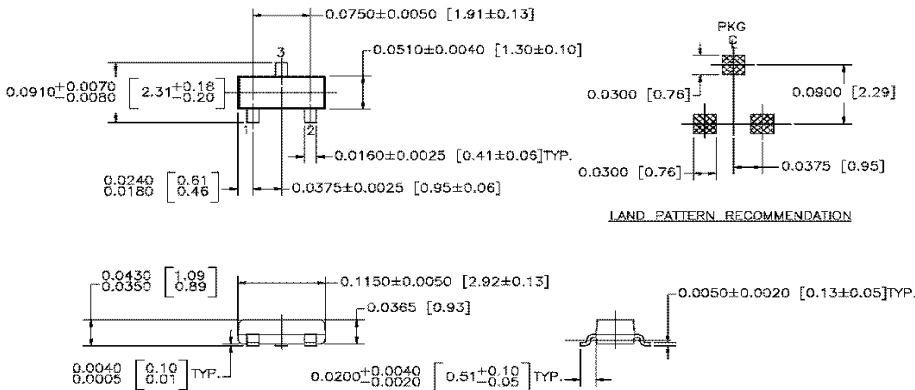
SOT-23



Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0082



CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS

SOT 23, 3 LEADS LOW PROFILE

NOTE : UNLESS OTHERWISE SPECIFIED

- STANDARD LEAD FINISH 150 MICRINCHES / 3.81 MICROMETERS
MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE C, DATED JUL 1993